

Reconsideration of the application is respectfully requested.

REMARKS

Claims 1-20 and 47 are pending in the present application. In the Office Action, claims 1, 7, 11, 17, and 47 was rejected under 35 U.S.C. § 102(e) as allegedly being anticipated by Yu (U.S. Patent No. 6,255,175). The Examiner's rejections are respectfully traversed.

With respect to independent claims 1, 11, and 47, Applicants describe and claim, among other things, forming a gate dielectric above a surface of the substrate and forming a doped-poly gate structure above the gate dielectric, the doped-poly gate structure having an edge region. Applicants also describe and claim forming a first dopant-depleted region in the edge region of the doped-poly gate structure adjacent the gate dielectric and a second dopant-depleted region in the substrate under the edge region of the doped-poly gate structure.

Yu describes forming a MOSFET 200 including a gate structure 206 formed above a substrate 102. Source and drain extensions 212, 214 are formed in the substrate such that a portion of the source and drain extensions 212, 214 extend beneath the gate structure 206. To minimize a parasitic Miller capacitance between the gate structure 206 and the source and drain extensions 212, 214, Yu describes forming first and second depletion regions 232, 234 by counter-doping sidewalls of the gate structure 206. However, Yu does not describe or suggest forming a second dopant-depleted region in the substrate under the edge region of the doped-poly gate structure. Thus, Applicants respectfully submit that claims 1, 7, 11, 17, and 47 are not anticipated by Yu and request that the Examiner's rejections of these claims under 35 U.S.C. § 102(e) be withdrawn.

In the Office Action, claims 4, 10, 14, and 20 were rejected under 35 U.S.C. § 103(a) as allegedly being obvious over Yu in view of Thompson, et al (U.S. Patent No. 6,020,244). The Examiner's rejections are respectfully traversed.

According to MPEP §706.02(l)(1), "effective November 29, 1999, subject matter which was prior art under former 35 U.S.C. 103 via 35 U.S.C. 102(e) is now disqualified as prior art against the claimed invention if that subject matter and the claimed invention 'were, at the time the invention was made, owned by the same person or subject to an obligation of assignment to the same person.' " The present application was filed on or after November 29, 1999. Furthermore, the present application and Yu were, at the time the present invention was made, owned by the same entity or subject to an obligation of assignment to the same entity. Thus, Applicants respectfully submit that Yu is not available as prior art in any obviousness determination and request that the Examiner's rejection of claims 4, 10, 14, and 20 under 35 U.S.C. § 103(a) be withdrawn.

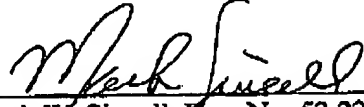
In the Office Action, the Examiner indicated that claims 2-3, 5-6, 8-9, 12-13, 15-16, and 18-19 contain allowable subject matter. Pursuant to the above arguments, Applicants respectfully submit that these claims are in condition for allowance.

For the aforementioned reasons, it is respectfully submitted that all claims pending in the present application are in condition for allowance. The Examiner is invited to contact the undersigned at (713) 934-4052 with any questions, comments or suggestions relating to the referenced patent application.

Respectfully submitted,

Date: _____

8/5/03


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